

AMENDMENTS TO THE DRAWINGS:

The replacement sheet in the Appendix includes changes to Figure 6. In Figure 6, the previously omitted designation "Prior Art" has been added.

REMARKS

Figure 6 has been amended to make an editorial change therein.

Claims 1-11 were rejected under §112, first paragraph. Paragraphs 0038-0040 of the application as filed describe how one of skill in the art would be able to form the source and drain regions of the present invention. The Official Action does not address these paragraphs and thus it cannot be determined whether these paragraphs are deemed to be inadequate or some other basis for the rejection exists. If the rejection is repeated, it is requested that a more detailed explanation be provided so that applicant can address the issues in detail. In any event, it is believed that one of skill in the art will be able to make and use the invention based on the present description. Reconsideration and withdrawal of the rejection are respectfully requested.

By way of further explanation, the statement in the Official Action that the source region and the drain region of the present invention are not isolated by isolation material is accurate. But, as shown in Figure 1 (and in amended claim 1), they are isolated physically by a semiconductor region whose conductivity type is different from those of the source and drain regions. Further, they are electrically isolated when the PN junction is reverse-biased, because they are formed by semiconductor material with different conductivity type, which is

apparent for those skilled in the art, for example, engineers working in the semiconductor industry with MOS technology.

Claims 1-11 were rejected as anticipated by SOLOMON et al. 6,437,422. Reconsideration and withdrawal of the rejection are respectfully requested.

Claim 1 has been amended. Support for the amendment is found in paragraph 0033.

SOLOMON et al. do not describe a linear device where the semiconductor region is arranged between the source region and the drain region, in a radial direction within a cross section of a device region, so that a part of the gate insulating region is in contact with the semiconductor region, where the semiconductor region is made of a semiconductor material having a different conductivity type than those of the source and drain regions. It is not seen that SOLOMON et al. disclose the different conductivity types claimed. Accordingly, the amended claims avoid this rejection under §102.

Claims 1-11 were rejected as anticipated by KASAMA et al. JP 2004-193437. KASAMA et al. was published on August 7, 2004. The present application claims priority to Japanese application 2003-321027 filed September 12, 2003, a date that is earlier than the publication date of KASAMA et al. A verified English translation of the priority Japanese application is provided in the Appendix to perfect the claim to priority. As is apparent, this priority application supports the application as

filed and thus there is no need to file a translation of the other priority application. Accordingly, KASAMA et al. is not prior art and reconsideration and withdrawal of this rejection under §102 are respectfully requested.

Please note that KASAMA et al. corresponds to PCT/JP03/15975 filed December 12, 2003, which entered the National Stage in the U.S. as S.N. 10/538,937 that was published July 27, 2006 as 2006/0162474. The perfected claim of priority allows the present application to avoid these references as well.

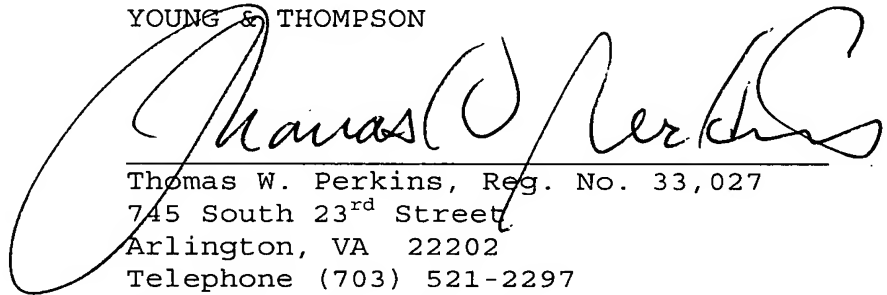
New claims 12-17 have been added and find support in Figures 1a-1f. These claims are allowable because SOLOMON et al. disclose a linear device with plural separate threads, while the invention of the new claims includes a multilayered linear device.

In view of the present amendment and the foregoing remarks, it is believed that the present application has been placed in condition for allowance. Reconsideration and allowance are respectfully requested.

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

YOUNG & THOMPSON

A large, stylized handwritten signature in black ink, appearing to read "Thomas W. Perkins", is written over the printed name and address.

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TWP/lrs

APPENDIX:

The Appendix includes the following items:

- one replacement drawing sheet, and
- a verified English translation of the priority

Japanese application 2003-321027 filed September 12, 2003.